



2DB1182Q

32V PNP MEDIUM POWER TRANSISTOR IN TO252

Features

- BV_{CEO} > -32V
- I_C = -2A High Continuous Collector Current
- I_{CM} = -3A Peak Pulse Current
- Epitaxial Planar Die Construction
- Low Collector-Emitter Saturation Voltage
- Ideal for Medium Power Switching or Amplification Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

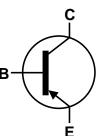
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.34 grams (Approximate)

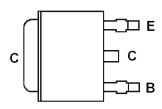








Device Schematic



Pin Out Configuration Top view

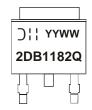
Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
2DB1182Q-13	AEC-Q101	2DB1182Q	13	16	2,500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



2DB1182Q = Product Type Marking Code

Old = Manufacturers' code marking

YYWW = Date Code Marking

YY = Last Digit of Year, (ex: 14 = 2014)

WW = Week Code 01-52

2DB1182Q Document number: DS35651 Rev. 3 - 2 1 of 6



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-32	V
Emitter-Base Voltage	V _{EBO}	-5	V
Continuous Collector Current	lc	-2	Α
Peak Pulse Collector Current	I _{CM}	-3	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	P _D	1.2	W
Power Dissipation @T _L = +25°C	(Note 6)	P _D	15	W
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	104	°C/W
Thermal Resistance, Junction to Lead	(Note 6)	$R_{\theta JL}$	8.3	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Note:

- 5. For a device mounted with the exposed collector pad on minimum recommended pad (MRP) layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

 6. Thermal resistance from junction to solder-point (on the exposed collector pad).
- 7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics

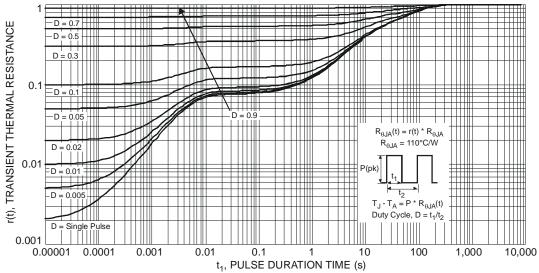


Figure 1 Transient Thermal Response

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Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Collector-Base Breakdown Voltage	BV _{CBO}	-40	_	_	V	$I_C = -50\mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage	BV _{CEO}	-32	_	_	V	$I_C = -1 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	_	_	V	$I_E = -50 \mu A, I_C = 0$	
Collector Cutoff Current	I _{CBO}	_	_	-1	μΑ	V _{CB} = -20V, I _E = 0	
Emitter Cutoff Current	I _{EBO}		_	-1	μΑ	V _{EB} = - 4V, I _C = 0	
ON CHARACTERISTICS (Note 8)							
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.8	V	$I_C = -2A$, $I_B = -0.2A$	
DC Current Gain	h _{FE}	120	_	270	_	$V_{CE} = -3V, I_{C} = -0.5A$	
SMALL SIGNAL CHARACTERISTICS							
Current Gain-Bandwidth Product	f _T	_	110	_	MHz	$V_{CE} = -5V, I_{C} = -0.1A,$ f = 30MHz	
Output Capacitance	C_{obo}	_	26	_	pF	V _{CB} = -10V, f = 1MHz	
Turn-On Time	ton	_	109	_	ns		
Delay Time	t _d	1	60	1	ns		
Rise Time	t _r		49	1	ns	Vcc = 30V	
Turn-Off Time	t _{off}		280	1	ns	$I_{CC} = 150 \text{mA}$ $I_{B1} = -I_{B2} = 15 \text{mA}$	
Storage Time	ts		246		ns	181 - 182 - 131114	
Fall Time	t _f	_	34	_	ns		

Note:

8. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

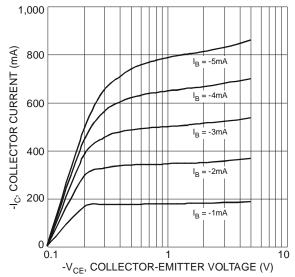


Figure 2 Typical Collector Current vs. Collector-Emitter Voltage

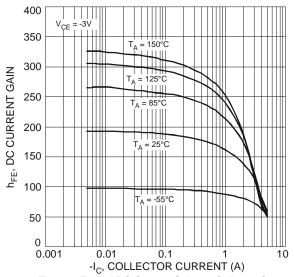


Figure 3 Typical DC Current Gain vs. Collector Current



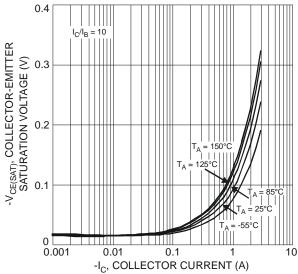


Figure 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

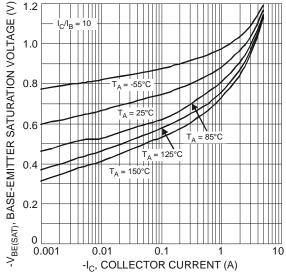


Figure 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

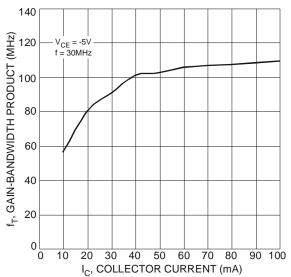


Figure 8 Typical Gain-Bandwidth Product vs. Collector Current

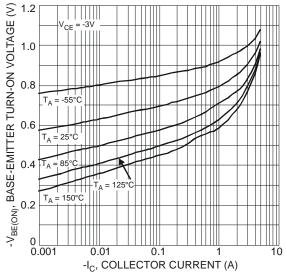


Figure 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

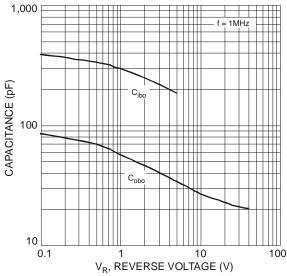
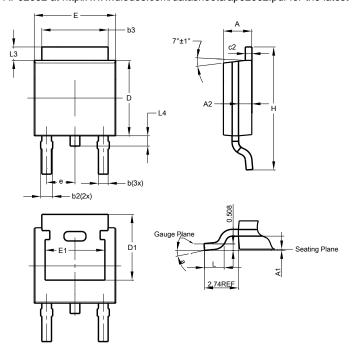


Figure 7 Typical Capacitance Characteristics



Package Outline Dimensions

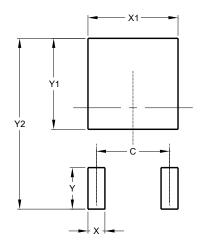
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
c2	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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6 of 6 2DB1182Q November 2014 Document number: DS35651 Rev. 3 - 2 © Diodes Incorporated

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